BIRLA INSTITUTE OF TECHNOLOGY AND SCIENCE, PILANI HYDERABAD CAMPUS

FIRST SEMESTER 2020-2021

Course Handout Part II

Date: 20/08/2021

In addition to part -I (General Handout for all courses appended to the Time Table), this portion gives further specific details regarding the course.

Course No. : EEE F214 / ECE F214 / INSTR F214

Course Title : Electronic Devices Instructor-in-Charge : Sayan Kanungo

Lecture Instructors : Sayan Kanungo & BVVSN Prabhakar Rao

Tutorial Instructors : Sayan Kanungo, BVVSN Prabhakar Rao & Parikshit

Sahatiya

1. Scope and Learning Outcome:

- i. Understanding the relationship between atomic structure and physical properties of semiconductors.
- ii. Interpreting electronic band structure using quantum mechanics.
- iii. Identifying the semiconductor properties that determine the performance of electronic devices.
- iv. Calculating the carrier concentrations and conductivity of a semiconductor using given doping concentrations.
- v. Understanding the basic physics of charge carriers in solids and carrier transport in semiconductors.
- vi. Deriving equations of charge transport in semiconductors under normal operating conditions.
- vii. Applying the charge transport equation to electronic devices and deriving their I-V characteristics.
- viii. Utilizing defect densities and carrier recombination processes to calculate generation and recombination rates in semiconductor devices.
- ix. Understanding the basics of optoelectronic devices.

2. Text Book:

- T1. B. G. Streetman, and Sanjay Banerjee, "Solid State Electronic Devices", 6th Ed., PHI, 2006.
- T2. D A. Neaman, "Semiconductor Physics and Devices", 4th Ed, Tata Mc Graw Hill.

3. Reference Book:

R1. Mark Lundstrom "Fundamental of nano-transistors Lessons from Nanoscience" World Scientific Book.

4. Course Plan:

| Lecture Topics to be covered No. | | Learning objectives | Chapter in the Text Book | |
|----------------------------------|--|---|---|--|
| 1 | Introduction to the subject and course details | | | |
| 2-3 | Review of semiconductor fundamentals | Basic overview of atoms, molecules and crystals, E-k diagram | 3.1.2 - 3.1.4 (T1) + 3.1.1, 3.1.3 (T2) | |
| 4-9 | Charge carriers in semiconductors | Intrinsic and Extrinsic Semiconductors, Direct and Indirect Band-gap Semiconductors, Effective Mass, Fermi level, Density of states, Equilibrium carrier concentrations, Band Diagram, Temperature dependence | 3.2.1-3.2.5, 3.3.1, 3.4.1-3.4.2, 3.5.2-3.5.3, 4.1.1-4.1.4, 4.2.1-4.2.3, 4.3.1-4.3.2, 4.3.4, 4.5.2, 4.6.2 (T2) | |
| 10-13 | Excess carriers in semiconductors | Interaction of photons with semiconductors, generation and recombination mechanisms of excess carriers, quasi-fermi levels in non-equilibrium | 4.1.1, 4.3.1-4.3.3 (T1) + 6.1.1-6.1.2 (T2) | |
| 14-16 | Charge carrier transport | Drift and Diffusion Transport, Mobility, Velocity Saturation, Conductivity | 3.4.1- 3.4.4, 4.4.1 - 4.4.3, 4.4.6 (T1) | |
| 17-24 | PN Junctions | PN junctions, Equilibrium, Biasing, I-V characteristics, Reverse bias breakdown, Tunnel Diode | 5.2 – 5.4, 10.1 (T1) + 7.2-7.3, 8.1, 8.4 (T2) | |
| 25-27 | Metal-Semiconductor Junctions (Ohmic/Schottky) | Ohmic & Schottky junctions: Equilibrium, Biasing for both p- and n- type semiconductors | 5.7 (T1) + 9.1.1-9.1.4, 9.2.1-9.2.2 (T2) | |
| 28-30 | Heterojunctions and Basic Concepts of BJT | Heterojunction Energy Band Structure, Working Principe of BJT | 9.31-9.3.2 (T2) + 7.1 (T1) | |
| 31-38 | Metal Oxide Semiconductor Field Effect Transistors | MOS Capacitor, Flat band Condition C-V Characteristics, Polysilicon/Metal Gates, Working principle of MOSFET, I-V characteristics, Effect of Body Bias, Short Channel Effects, Velocity Saturation Effect | 11.1.1 - 11.1.6, 11.2.1 - 11.2.3, 11.3.1 - 11.3.2, 12.1.1 -12.1.4, 12.3.1 (T2) + relevant sections from reference book | |
| 39-40 | Optoelectronic devices | Solar cells, Photodiode | 14.2.1-14.2.2, 14.3.2- 14.3.3 (T2) | |

5. Evaluation Scheme:

| Component | Duration | Weightage | Marks (200) | Date & Time | Nature of Component |
|---------------|----------|-----------|-------------|-----------------|---------------------|
| | | | (%) | | |
| Quizzes | 30 min | 30% | 60 | TBA | Open Book |
| Mid-semester | TBA | 30% | 60 | 22/10/2021 9.00 | Open Book |
| Exam. | | | | - 10.30AM | |
| Comprehensive | TBA | 40% | 80 | 22/12 AN | Open Book |
| Exam. | | | | | _ |
| Total | | 100% | 200 | | |

- **6. Chamber Consultation hours**: To be announced in the class.
- **7. Notices**: All notices for the course will be announced in the class and <u>displayed only on the CMS</u>.

Make-up Policy: Requests for make-up examination will be conducted ONLY for genuine cases for midsemester and comprehensive examination.

Academic Honesty and Integrity Policy: Academic honesty and integrity are to be maintained by all the students throughout the semester and no type of academic dishonesty is acceptable.

Instructor-in-Charge Sayan Kanungo